

DMP32D4S

30V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on)} Max	I _D Max @T _A = +25°C
-30V	2.4Ω @ V _{GS} = -10V	-300mA
	4Ω @ V _{GS} = -4.5V	-250mA

Description

This MOSFET has been designed to minimize the on-state resistance $(R_{DS(ON)})$ and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Load Switch
- Portable Applications
- Power Management Functions

Features

- Low On-Resistance
- ESD Protected Gate to 2kV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

Case: SOT23

D

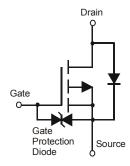
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe). (3)
- Weight: 0.006 grams (approximate)





SOT23





Equivalent Circuit

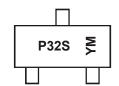
Ordering Information (Note 4)

Part Number	Case	Packaging
DMP32D4S-7	SOT23	3,000/Tape & Reel
DMP32D4S-13	SOT23	10,000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



P32S = Product Type Marking Code YM = Date Code Marking Y = Year (ex: Z = 2012)

M = Month (ex: 9 = September)

Date Code Key

Year	201	2	2013		2014	20	15	2016		2017	2	2018
Code	Z		Α		В	(2	D		E		F
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Character	ristic		Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-30	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 6) $V_{GS} = -10V$ $T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$		I _D	300 250	mA	
Pulsed Drain Current (Note 6)			I _{DM}	-1	Α

Thermal Characteristics @TA = 25°C unless otherwise specified

Characteristic		Symbol	Value	Units	
Total Dawer Dissination	(Note 5)	ם	370	mW	
Total Power Dissipation	(Note 6)	P_D	540		
Thermal Resistance, Junction to Ambient	(Note 5)	_	348		
memai Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	241	°C/W	
Thermal Resistance, Junction to Case	(Note 6)	R _{eJC}	91		
Operating and Storage Temperature Range		$T_{J_i} T_{STG}$	-55 to +150	°C	

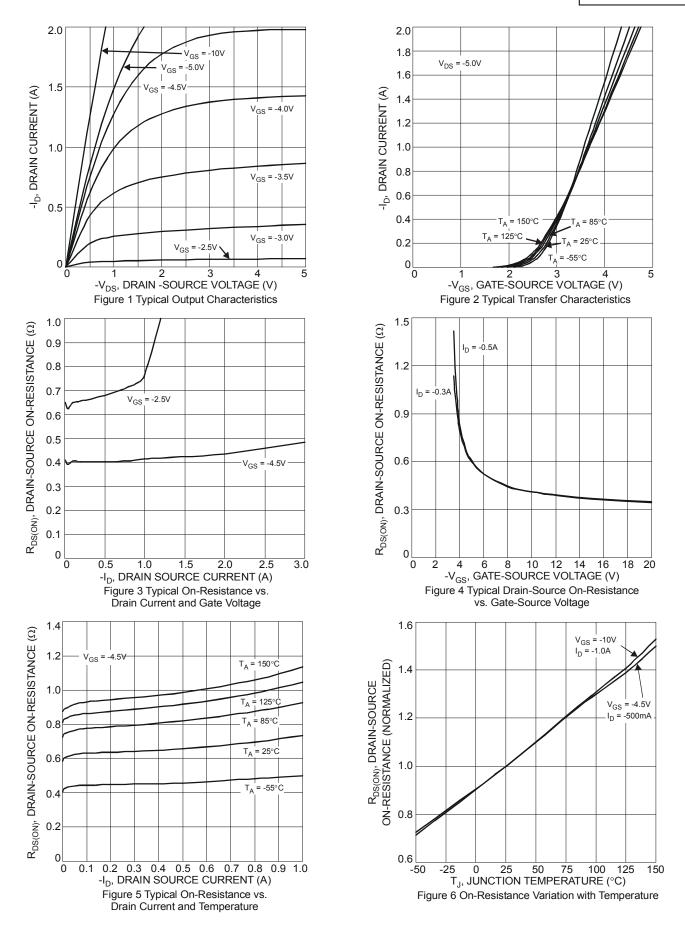
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 7)						_		
Drain-Source Breakdown Voltage	BV _{DSS}	-30	_	_	V	$V_{GS} = 0V$, $I_D = -1mA$		
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	_	_	-1	μΑ	$V_{DS} = -30V, V_{GS} = 0V$		
Gate-Source Leakage	I_{GSS}	_	_	±10	μA	$V_{GS} = \pm 16V, V_{DS} = 0V$		
ON CHARACTERISTICS (Note 7)								
Gate Threshold Voltage	Vasuu	-1.4	_	-2.4	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$		
Gate Threshold Voltage	V _{GS(th)}	-1.2	_	-2.0	٧	$V_{DS} = -5V, I_{D} = -1\mu A$		
Static Drain-Source On-Resistance	Pro (ON)			2.4	Ω	$V_{GS} = -10V$, $I_D = -0.3A$		
Otatic Brain-Oddrec Off-Nesistance	R _{DS (ON)}			4	1 12	$V_{GS} = -4.5V$, $I_D = -0.25A$		
Forward Transfer Admittance	Y _{fs}	_	6	_	S	$V_{DS} = -10V$, $I_D = -400$ mA		
Diode Forward Voltage	V_{SD}	_	8.0	1.2	V	$V_{GS} = 0V, I_S = -300mA$		
DYNAMIC CHARACTERISTICS (Note 8)								
Input Capacitance	C _{iss}	_	51.16		pF	15)/)/ 0)/		
Output Capacitance	Coss	1	10.85	1	pF	$V_{DS} = -15V, V_{GS} = 0V,$ -f = 1.0MHz		
Reverse Transfer Capacitance	Crss	_	8.88	_	pF	1 - 1.0WH12		
Gate Resistance	R_g	_	275	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$		
Total Gate Charge	Qg	_	0.6	_	nC	V _{GS} = -4.5V		
Total Gate Charge	Qg	_	1.2	_	nC	V _{DS} = -10V,		
Gate-Source Charge	Q _{gs}	_	0.2	_	nC	V _{GS} = -10V I _D = -1A		
Gate-Drain Charge	Q _{gd}	_	0.3	_	nC	1		
Turn-On Delay Time	t _{D(on)}	_	9.86	_	ns	·		
Turn-On Rise Time	t _r	_	11.5	_	ns	V _{DS} = -15V, I _D = -1A		
Turn-Off Delay Time	$t_{D(off)}$	_	31.8	_	ns	V_{GS} = -10V, R_G = 6Ω		
Turn-Off Fall Time	t _f	_	21.9	_	ns	7		

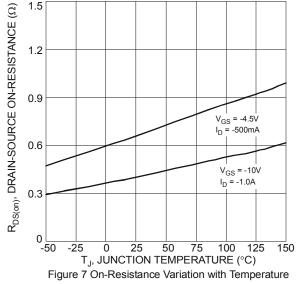
Notes:

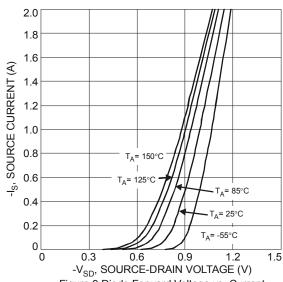
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout 7. Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to production testing.

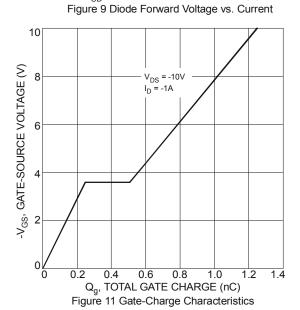












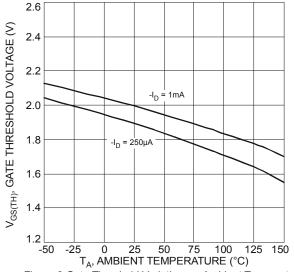
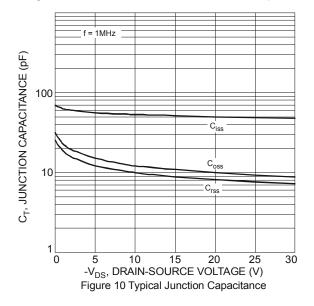


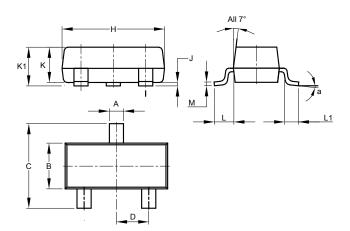
Figure 8 Gate Threshold Variation vs. Ambient Temperature





Package Outline Dimensions

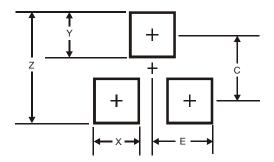
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT23								
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
С	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
Н	2.80	3.00	2.90					
7	0.013	0.10	0.05					
K	0.890	1.00	0.975					
K1	0.903	1.10	1.025					
L	0.45	0.61	0.55					
L1	0.25	0.55	0.40					
М	0.085	0.150	0.110					
а	8°							
All	All Dimensions in mm							

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
X	0.8
Υ	0.9
С	2.0
E	1.35



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